

关键参数		Key Parameters	
V_{CES}		750	V
$V_{CE(sat)}$	Typ.	1.70	V
I_C	Max.	400	A
$I_{C(RM)}$	Max.	800	A

典型应用		Typical Applications	
● 电动汽车应用		Automotive applications	
● 混合动力/纯电动车		Hybrid/Electrical vehicles	
● 电机驱动		Motor drives	

特点	Features
● 铜基板	Cu baseplate
● 增强型氧化铝衬板	Enhanced Al_2O_3 substrates
● 750V 额定电压	Blocking Voltage 750V
● 高电流密度	High current density

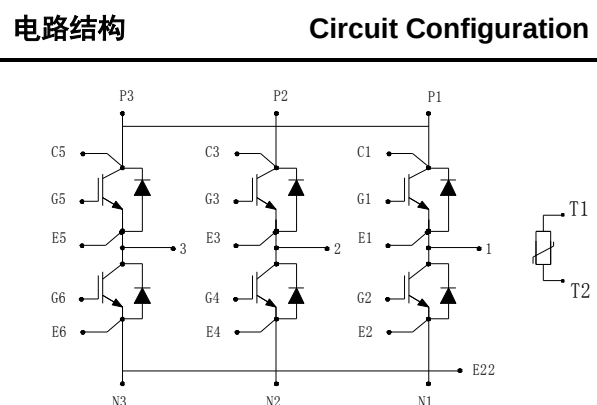


图 1. 电路结构

Fig. 1 Circuit configuration

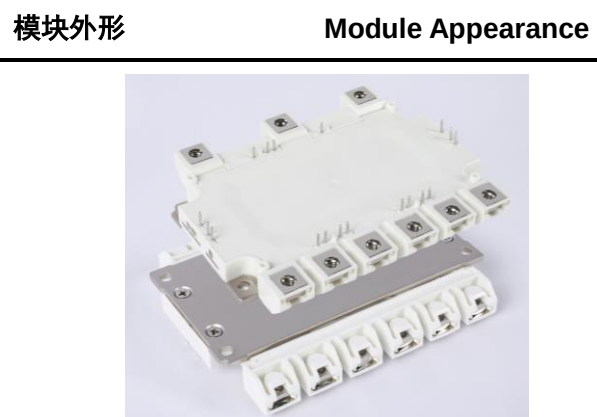


图 2. 模块外形

Fig. 2 Module appearance

模块标签说明		Module Label Code Instruction	
	数据位置	数据内容	
	Data position	Content of data	
	1—8	模块批次号	
		Module batch number	
	9—12	模块序列号	
		Module serial number	

最大额定值
Absolute Maximum Ratings

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	数值 Value	单位 Unit
V_{CES}	集电极-发射极电压 Collector-emitter voltage	$V_{GE} = 0V, T_C = 25\text{ }^{\circ}\text{C}$	750	V
V_{GES}	栅极-发射极电压 Gate-emitter voltage	$T_C = 25\text{ }^{\circ}\text{C}$	± 20	V
I_C	集电极电流 Collector-emitter current	$T_C = 65\text{ }^{\circ}\text{C}, T_{vj\text{ max}} = 175\text{ }^{\circ}\text{C}$	400	A
$I_{C(PK)}$	集电极峰值电流 Peak collector current	$t_P = 1\text{ms}$	800	A
P_{max}	晶体管部分最大损耗 Max. transistor power dissipation	$T_C = 25\text{ }^{\circ}\text{C}, T_{vj\text{ max}} = 175\text{ }^{\circ}\text{C}$	1250	W
I^2t	二极管 I^2t 值 Diode I^2t	$V_R = 0V, t_P = 10\text{ms}, T_{vj} = 150\text{ }^{\circ}\text{C}$	8500	A^2s
V_{isol}	绝缘电压(模块) Isolation voltage – per module	短接所有端子，端子与基板间施加电压 (Commoned terminals to baseplate), AC RMS, 1 min, 50Hz, $T_C = 25\text{ }^{\circ}\text{C}$	2500	V

热和机械数据
Thermal & Mechanical Data

参数 Symbol	说明 Explanation	值 Value	单位 Unit
爬电距离 Creepage distance	端子-散热器 Terminal to heatsink	12	mm
	端子-端子 Terminal to terminal	6.1	mm
绝缘间隙 Clearance	端子-散热器 Terminal to heatsink	12	mm
	端子-端子 Terminal to terminal	6.1	mm
相对漏电起痕指数 CTI (Comparativetrackingindex)		>200	

热和机械数据
Thermal & Mechanical Data

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
$R_{th(J-C)}_{IGBT}$	IGBT 结壳热阻 Thermal resistance – IGBT				120	K / kW
$R_{th(J-C)}_{Diode}$	二极管结壳热阻 Thermal resistance – Diode				200	K / kW
$R_{th(C-H)}_{IGBT}$	接触热阻(IGBT) Thermal resistance – case to heatsink (IGBT)	安装力矩 5Nm, 导热脂 1W/m·°C Mounting torque 5Nm, with mounting grease 1W/m·°C		80		K / kW
$R_{th(C-H)}_{Diode}$	接触热阻(Diode) Thermal resistance – case to heatsink (Diode)	安装力矩 5Nm, 导热脂 1W/m·°C Mounting torque 5Nm, with mounting grease 1W/m·°C		85		K / kW
$T_{vj\ op}$	工作结温 Operating junction temperature	IGBT 部分 (IGBT)	-40		150	°C
		二极管部分 (Diode)	-40		150	°C
T_{stg}	存储温度 Storage temperature range		-40		125	°C
M	安装力矩 Screw torque	安装紧固用– M5 Mounting – M5	3		6	Nm
		电路互连用– M6 Electrical connections – M6	3		6	Nm

热敏电阻数据
NTC-Thermistor Data

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
R_{25}	额定电阻值 Rated resistance	$T_C = 25\ ^\circ\text{C}$		5		kΩ
$\Delta R/R$	R100 偏差 Deviation of R100	$T_C = 100\ ^\circ\text{C}$, $R_{100}=493\Omega$	-5		5	%
P_{25}	耗散功率 Power dissipation	$T_C = 25\ ^\circ\text{C}$			20	mW
$B_{25/50}$	B-值 B-value	$R_2 = R_{25}\exp [B_{25/50}(1/T_2 - 1/(298.15\text{ K}))]$		3375		K
$B_{25/80}$	B-值 B-value	$R_2 = R_{25}\exp [B_{25/80}(1/T_2 - 1/(298.15\text{ K}))]$		3411		K
$B_{25/100}$	B-值 B-value	$R_2 = R_{25}\exp [B_{25/100}(1/T_2 - 1/(298.15\text{ K}))]$		3433		K

Caution: This device is sensitive to electrostatic discharge. Users should follow ESD handling procedures.

注意：该器件对静电敏感，用户须采取 ESD 防护措施。

电特性值
Electrical Characteristics

除非特别声明，否则 $T_C = 25\text{ }^{\circ}\text{C}$
 $T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise stated

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
I_{CES}	集电极截止电流 Collector cut-off current	$V_{GE} = 0V, V_{CE} = V_{CES}$			1	mA
		$V_{GE} = 0V, V_{CE} = V_{CES}, T_C = 125\text{ }^{\circ}\text{C}$			10	mA
		$V_{GE} = 0V, V_{CE} = V_{CES}, T_C = 150\text{ }^{\circ}\text{C}$			15	mA
I_{GES}	栅极漏电流 Gate leakage current	$V_{GE} = \pm 20V, V_{CE} = 0V$			0.5	μA
$V_{GE(TH)}$	栅极-发射极阈值电压 Gate threshold voltage	$I_C = 10\text{mA}, V_{GE} = V_{CE}$	5.30	5.90	6.50	V
$V_{CE(sat)}^{(*1)}$	集电极-发射极饱和电压 Collector-emitter saturation voltage	$V_{GE} = 15V, I_C = 400A$		1.70	2.10	V
		$V_{GE} = 15V, I_C = 400A, T_{vj} = 125\text{ }^{\circ}\text{C}$		1.95		V
		$V_{GE} = 15V, I_C = 400A, T_{vj} = 150\text{ }^{\circ}\text{C}$		2.00		V
I_F	二极管正向直流电流 Diode forward current	DC		400		A
I_{FRM}	二极管正向重复峰值电流 Diode peak forward current	$t_p = 1\text{ms}$		800		A
$V_F^{(*1)}$	二极管正向电压 Diode forward voltage	$I_F = 400A, V_{GE} = 0$		1.60	2.00	V
		$I_F = 400A, V_{GE} = 0, T_{vj} = 125\text{ }^{\circ}\text{C}$		1.70		V
		$I_F = 400A, V_{GE} = 0, T_{vj} = 150\text{ }^{\circ}\text{C}$		1.70		V
I_{SC}	短路电流 Short circuit current	$T_{vj} = 150\text{ }^{\circ}\text{C}, V_{CC} = 400V,$ $V_{GE} \leq 15V, t_p \leq 6\mu\text{s},$ $V_{CE(max)} = V_{CES} - L^{(*2)} \times di/dt,$ IEC 6074-9		1600		A

注意: 1. (*1) 表示该参数的测试点为辅助母排端子 (*1 indicates it is measured at the auxiliary busbar terminal),

Note: 2. (*2) 表示 L 是电路杂散电感加上 L_M (*2 indicates L is the circuit stray inductance plus L_M).

电特性值
Electrical Characteristics

 除非特别声明，否则 $T_C = 25\text{ }^{\circ}\text{C}$
 $T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise stated

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
C_{ies}	输入电容 Input capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 100kHz$		33		nF
Q_g	栅极电荷 Gate charge	$\pm 15V$		2.5		μC
C_{res}	反向传输电容 Reverse transfer capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 100kHz$		0.5		nF
L_M	模块电感 Module inductance			15		nH
R_{INT}	内阻 Internal transistor resistance			1		m Ω

电特性值
Electrical Characteristics

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions		最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
$t_{d(off)}$	关断延迟时间 Turn-off delay time	$I_C=400A$, $V_{CE}=400V$, $V_{GE}=\pm 15V$, $R_{G(OFF)}=1.8\Omega$, $L_S=50nH$, $dv/dt=6700V/us$ ($T_{vj}=150^{\circ}C$).	$T_{vj}=25^{\circ}C$		515		ns
			$T_{vj}=125^{\circ}C$		550		
			$T_{vj}=150^{\circ}C$		560		
t_f	下降时间 Fall time		$T_{vj}=25^{\circ}C$		60		ns
			$T_{vj}=125^{\circ}C$		75		
			$T_{vj}=150^{\circ}C$		85		
E_{OFF}	关断损耗 Turn-off energy loss		$T_{vj}=25^{\circ}C$		18.0		mJ
			$T_{vj}=125^{\circ}C$		21.0		
			$T_{vj}=150^{\circ}C$		23.0		
$t_{d(on)}$	开通延迟时间 Turn-on delay time	$I_C=400A$, $V_{CE}=400V$, $V_{GE}=\pm 15V$, $R_{G(ON)}=1.8\Omega$, $L_S=50nH$, $di/dt=6100A/us$ ($T_{vj}=150^{\circ}C$).	$T_{vj}=25^{\circ}C$		420		ns
			$T_{vj}=125^{\circ}C$		420		
			$T_{vj}=150^{\circ}C$		420		
t_r	上升时间 Rise time		$T_{vj}=25^{\circ}C$		65		ns
			$T_{vj}=125^{\circ}C$		70		
			$T_{vj}=150^{\circ}C$		70		
E_{ON}	开通损耗 Turn-on energy loss		$T_{vj}=25^{\circ}C$		4.5		mJ
			$T_{vj}=125^{\circ}C$		6.0		
			$T_{vj}=150^{\circ}C$		6.5		
Q_{rr}	二极管反向恢复电荷 Diode reverse recovery charge	$I_F=400A$, $V_{CE}=400V$, - $di_F/dt=6100A/us$ ($T_{vj}=150^{\circ}C$).	$T_{vj}=25^{\circ}C$		25		μC
			$T_{vj}=125^{\circ}C$		40		
			$T_{vj}=150^{\circ}C$		44		
I_{rr}	二极管反向恢复电流 Diode reverse recovery current		$T_{vj}=25^{\circ}C$		260		A
			$T_{vj}=125^{\circ}C$		295		
			$T_{vj}=150^{\circ}C$		300		
E_{rec}	二极管反向恢复损耗 Diode reverse recovery energy		$T_{vj}=25^{\circ}C$		8.5		mJ
			$T_{vj}=125^{\circ}C$		13.5		
			$T_{vj}=150^{\circ}C$		14.5		

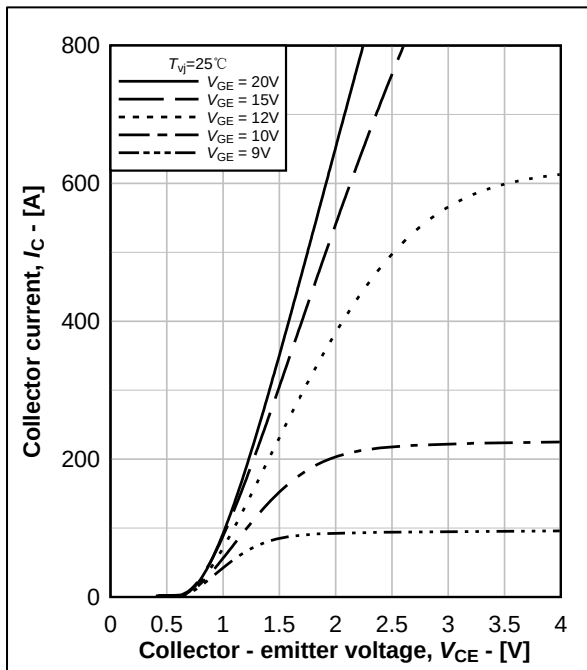

图 3. IGBT 输出特性典型曲线, $I_C = f(V_{CE})$

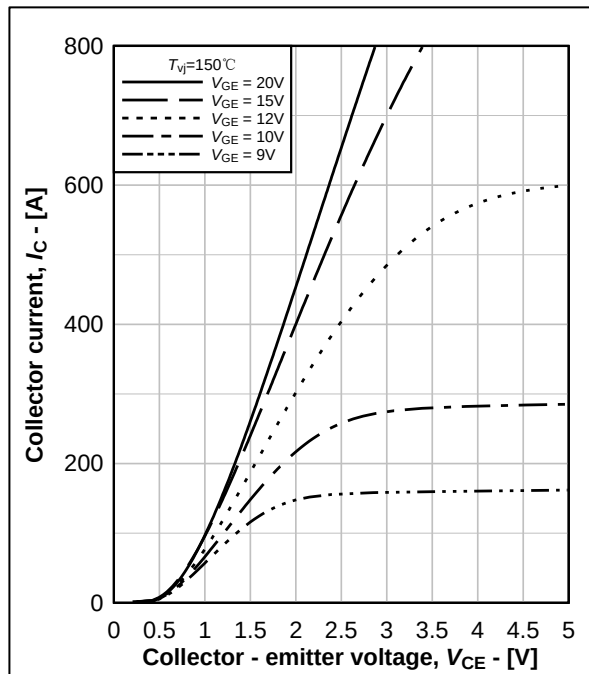
Fig.3 Typical IGBT output characteristics, $I_C = f(V_{CE})$

图 4. IGBT 输出特性典型曲线, $I_C = f(V_{CE})$

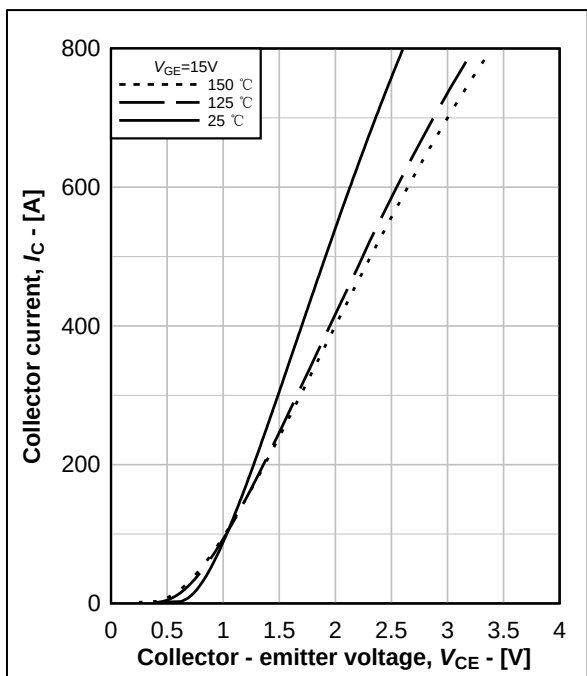
Fig.4 Typical IGBT output characteristics, $I_C = f(V_{CE})$

图 5. IGBT 输出特性典型曲线, $I_C = f(V_{CE})$

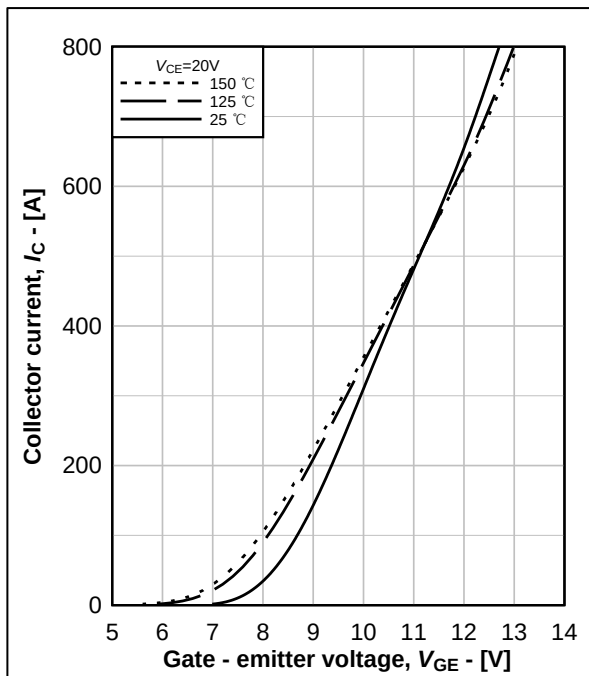
Fig.5 Typical IGBT output characteristics, $I_C = f(V_{CE})$

图 6. IGBT 传输特性典型曲线, $I_C = f(V_{GE})$

Fig.6 Typical IGBT transfer characteristics, $I_C = f(V_{GE})$

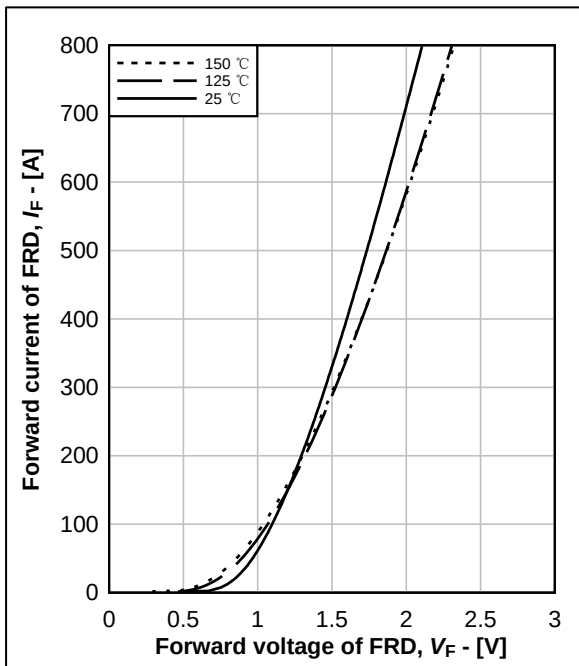

图 7. FRD 输出特性典型曲线, $I_F = f(V_F)$

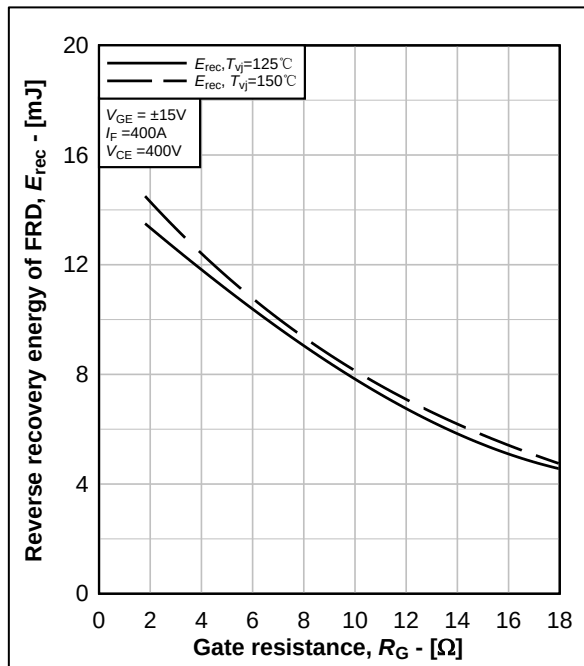
Fig.7 Typical FRD output characteristics, $I_F = f(V_F)$

图 8. FRD 反向恢复能耗典型曲线, $E_{rec} = f(R_G)$

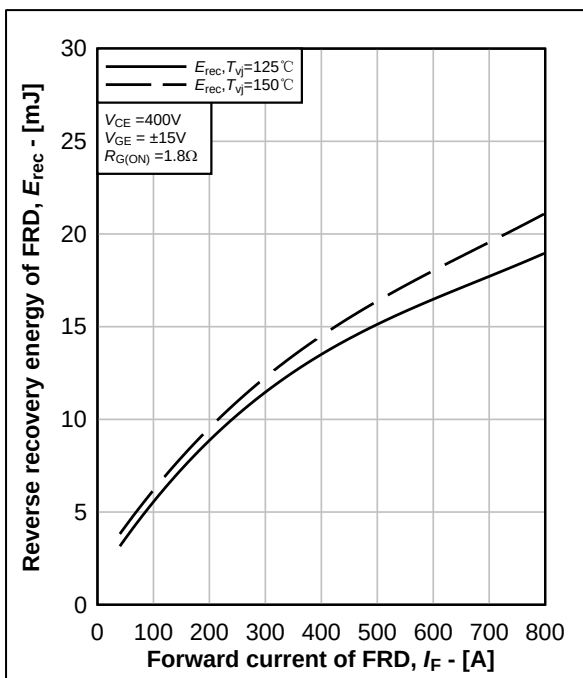
Fig.8 Typical FRD E_{rec} , $E_{rec} = f(R_G)$

图 9. FRD 反向恢复能耗典型曲线, $E_{rec} = f(I_F)$

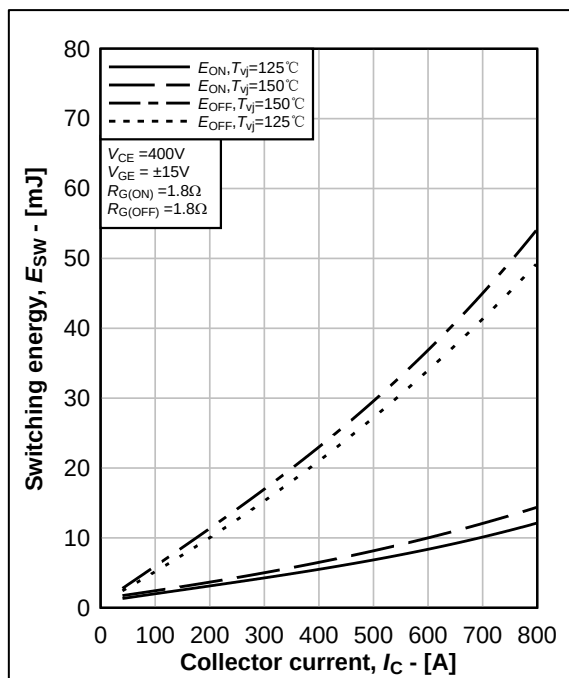
Fig.9 Typical FRD E_{rec} , $E_{rec} = f(I_F)$

图 10. IGBT 开关能耗典型曲线, $E_{on} = f(I_C)$, $E_{off} = f(I_C)$

Fig.10 Typical IGBT switching energy, $E_{on} = f(I_C)$, $E_{off} = f(I_C)$

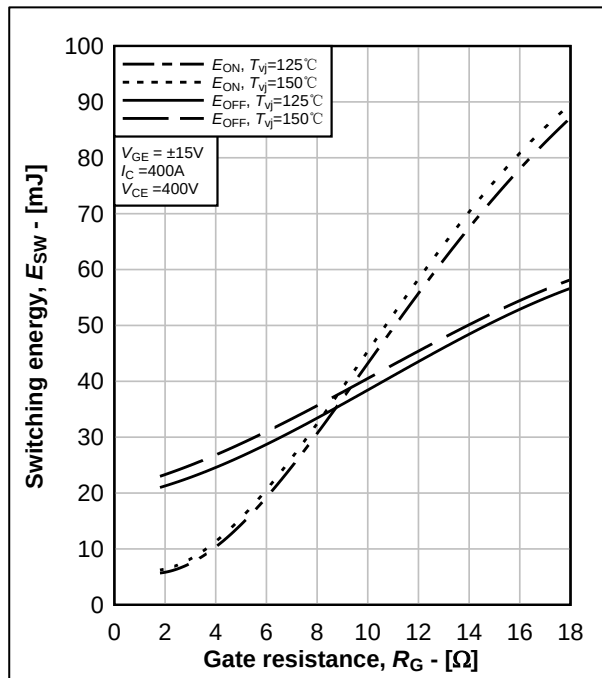

图 11. IGBT 开关能耗典型曲线, $E_{on}=f(R_G)$, $E_{off}=f(R_G)$

Fig.11 Typical IGBT switching energy,

$$E_{on}=f(R_G), E_{off}=f(R_G)$$

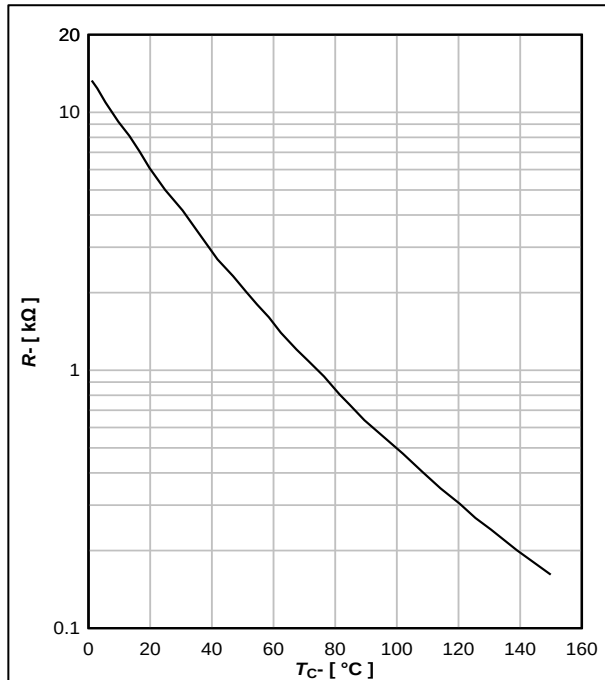

图 12. 热敏电阻典型特性曲线, $R=f(T_C)$

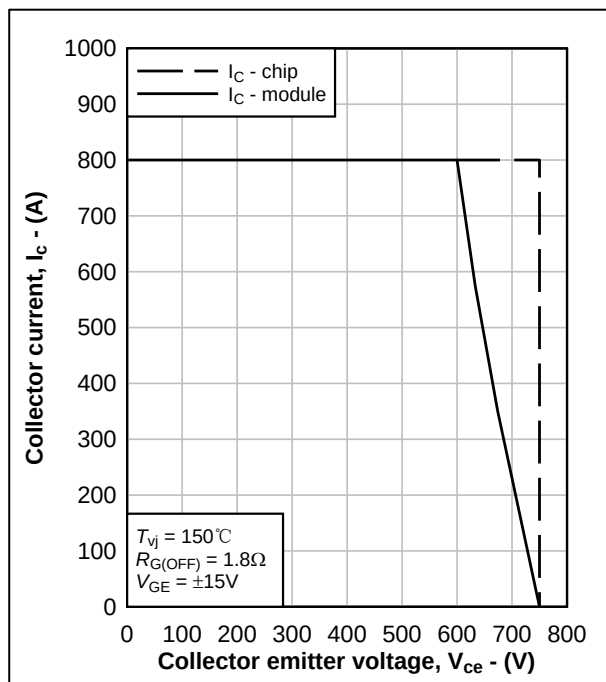
Fig.12 Typical NTC thermistor characteristic, $R=f(T_C)$

图 13. IGBT 反偏安全工作区, $I_C=f(V_{CE})$

Fig.13 Reverse bias safe operating area of IGBT,

$$I_C=f(V_{CE})$$

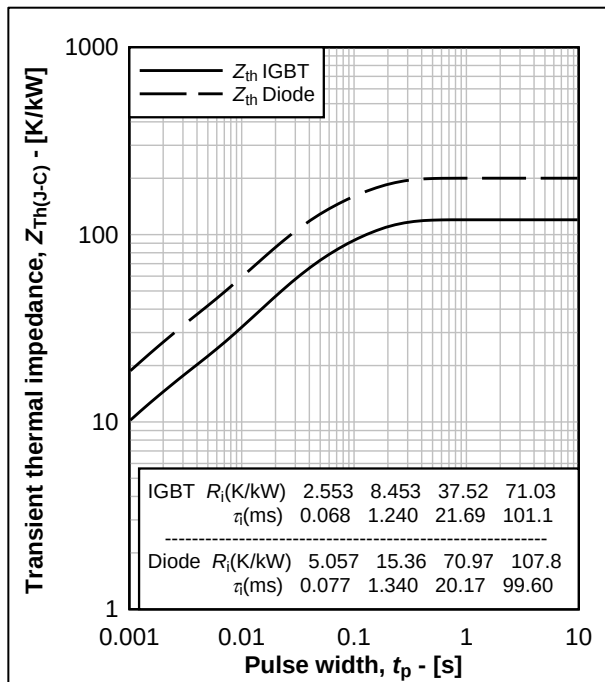
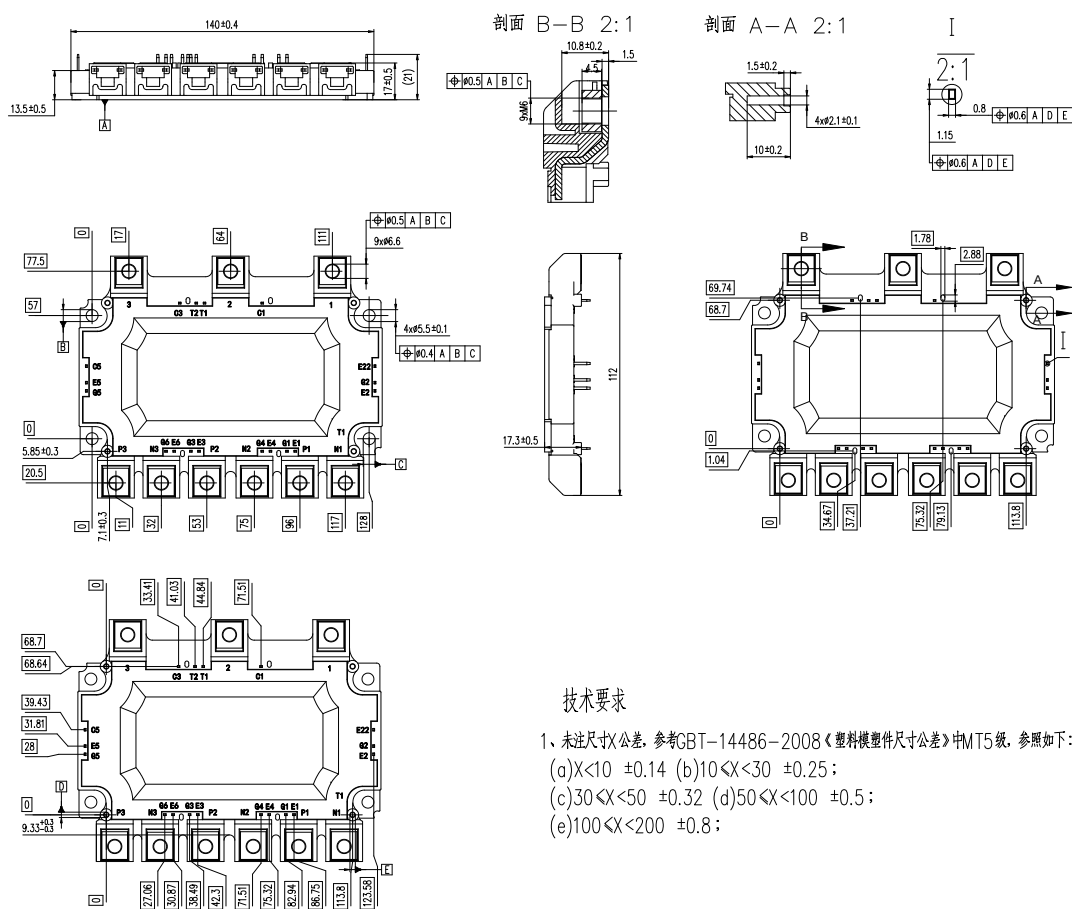

图 14. 瞬态热阻抗曲线, $Z_{Th(J-C)}=f(t_p)$

Fig.14 Transient thermal impedance, $Z_{Th(J-C)}=f(t_p)$



重量 Weight: 515g

模块外观类型 Module outline code: S2

图 15. 模块外观尺寸

Fig. 15 Module outlines

株洲中车时代半导体有限公司

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(6) We annotate datasheet in the top right hand corner of the front page, to indicate product status. The annotation “Preliminary” indicates the product design is complete and final characterization for volume production is in progress, the product information in the datasheet is currently can be referenced, but some details may change in the future. There is no annotation indicates the product is capable to produce in batch quantity.